

isc N-Channel MOSFET Transistor

2SK349

DESCRIPTION

- Drain Current $-I_D=10A @ T_C=25^\circ C$
- Drain Source Voltage-
: $V_{DSS}= 400V(\text{Min})$
- Fast Switching Speed

APPLICATIONS

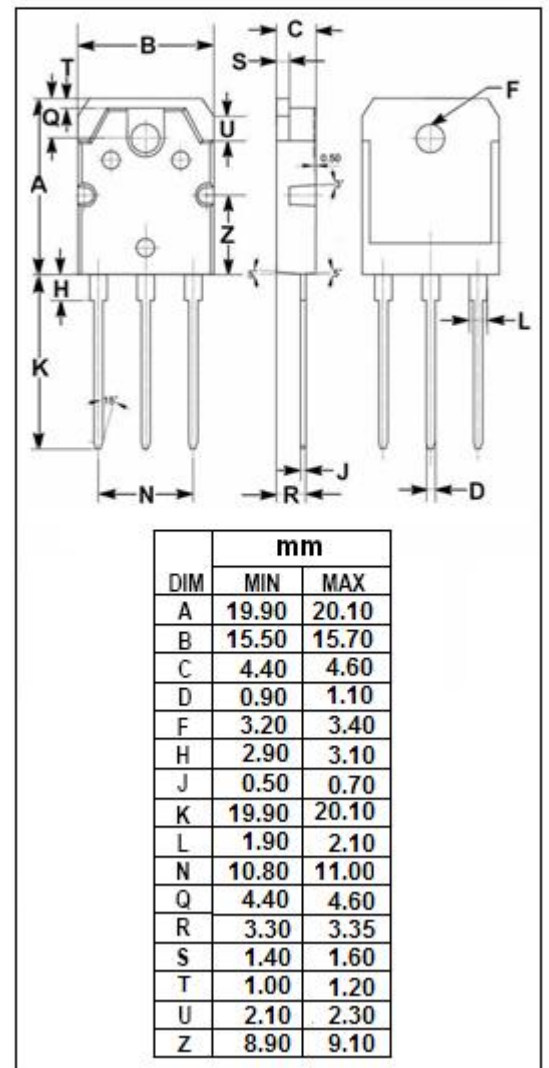
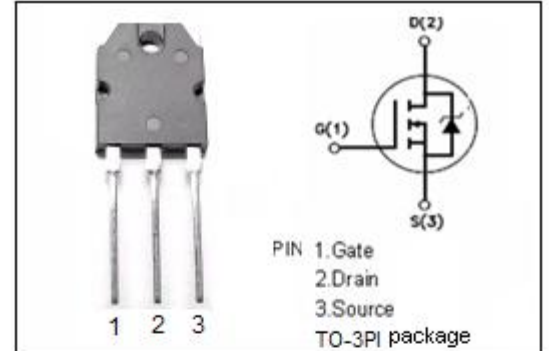
- low on-resistance.
- High speed switching.
- Low drive current.
- No secondary breakdown.
- Suitable for switching regulator, DC-DC control.

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage ($V_{GS}=0$)	400	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Drain Current-continuous@ $T_C=25^\circ C$	10	A
P_{tot}	Total Dissipation@ $T_C=25^\circ C$	100	W
T_j	Max. Operating Junction Temperature	150	$^\circ C$
T_{stg}	Storage Temperature Range	-55~150	$^\circ C$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	1.67	$^\circ C/W$
$R_{th\ j-a}$	Thermal Resistance, Junction to Ambient	62.5	$^\circ C/W$



isc N-Channel Mosfet Transistor**2SK349****• ELECTRICAL CHARACTERISTICS (T_C=25°C)**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0; I _D = 10mA	400			V
V _{GS(TH)}	Gate Threshold Voltage	V _{DS} = 10V _{GS} ; I _D = 1mA	1.0		5.0	V
R _{DS(ON)}	Drain-Source On-stage Resistance	V _{GS} = 15V; I _D = 5A		0.67	0.90	Ω
I _{GSS}	Gate Source Leakage Current	V _{GS} = ±20V; V _{DS} = 0			±1	uA
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =320V; V _{GS} = 0			1	mA
V _{SD}	Diode Forward Voltage	I _F = 5A; V _{GS} =0		0.85		V
t _r	Rise time	V _{GS} =15V; I _D =2A; R _L =15 Ω		50		ns
t _{on}	Turn-on time			70		ns
t _f	Fall time			60		ns
t _{off}	Turn-off time			200		ns